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- (54) Process for producing multilevel metallization in an integrated circuit
- (57) A method for fabricating a multi-level integrated circuit is disclosed which utilizes a grid pattern from which portions corresponding to the metal layer are selectively removed to form a mask which is subsequently

used to deposit dummy features in the open areas between metal lines, thereby to allow the deposition of a substantially planar dielectric surface over the metal layers and dummy features.



EUROPEAN SEARCH REPORT

Application Number EP 95 30 7802

Category	Citation of document with in of relevant pas		Relevant to claim	CLASSIFICATION OF THE APPLICATION (bl.CL6)
A	PATENT ABSTRACTS OF JAPAN vol. 011, no. 130 (E-502), 23 April 1987 & JP 61 276345 A (OKI ELECTRIC IND CO LTD), 6 December 1986, * abstract *		,	H01L21/768
•	PATENT ABSTRACTS OF vol. 013, no. 046 (& JP 63 240045 A (CO LTD), 5 October * abstract *	E-711), 2 February 1989 MATSUSHITA ELECTRIC IND		
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X : pas Y : pas	CATEGORY OF CITED DOCUMENT ricularly relevant if taken alone ricularly relevant if combined with and tument of the same category	E : earlier patent de after the filing	ple underlying the consent, but pul- fate in the application	blished on, or m